

PIII: GG and Microst. Evolution

Outline:

Types of grain growth: Stationary vs. Nonstationary

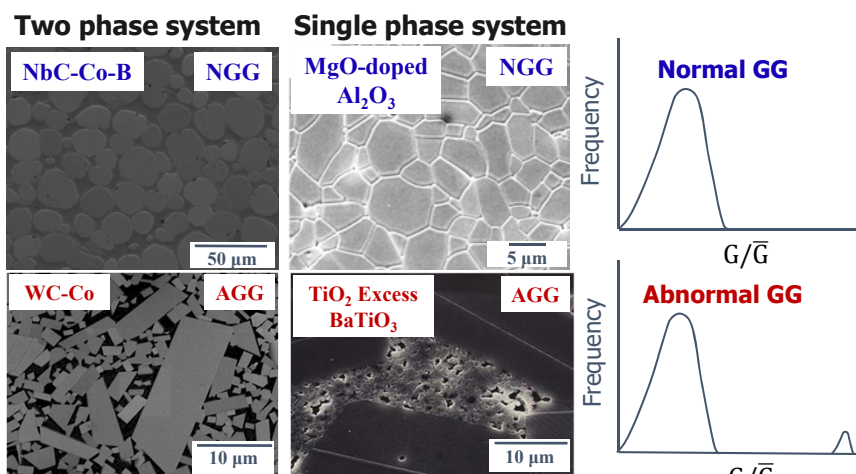
- Liquid phase sintering (LPS)
 - Grain growth in a matrix (Ostwald ripening)
 - Effect of pores on microstructure development
 - Effect of interfacial energy anisotropy
- Solid state sintering (SSS)
 - Grain growth in a pure dense system
 - Effect of 2nd phase particles on grain growth
 - Effect of pores on microstructure development
 - Effect of solute segregation on boundary migration
 - Effect of boundary energy anisotropy

Mixed Mechanism Principle of Microstructural Evolution

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Grain Growth and Microstructure

Two Extreme Cases: **Normal** and **Abnormal**



J. H. Lee, M.S. Thesis, (KAIST, 2005)
S. Y. Choi, Ph.D. Thesis, (KAIST, 2004)

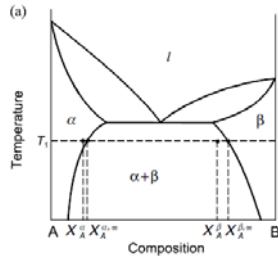
C. W. Park and D. Y. Yoon, *J. Am. Ceram. Soc.*, **83**, 2605 (2000).
D. Y. Yang and S.-J. L. Kang, *Int. J. Refract. H. Mater.*, **27**, 90 (2009)

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Chap. Liquid Phase Sintering

Qn: Why grain growth takes place during sintering?

Driving Force



$$X_A^\beta = X_A^{\beta,\infty} \left(1 + \frac{1 - X_A^{\beta,\infty}}{X_A^{\alpha,\infty} - X_A^{\beta,\infty}} \frac{\gamma V^\alpha K}{RT} \right)$$

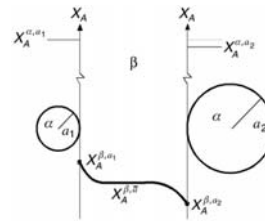
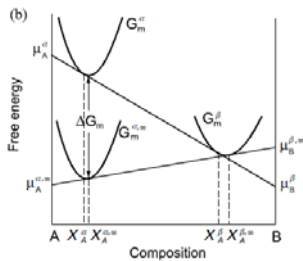


Figure 15.1. (a) Typical phase diagram showing limited solubility of $X_A^{\alpha,\infty}$ and $X_B^{\beta,\infty}$ at temperature T_e and (b) schematic of the molar free energy versus composition at the temperature for α precipitates with a flat interface ($K=0$) and with a finite radius of curvature ($K \neq 0$).

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Lifshitz-Slyozov-Wagner (LSW) Theory

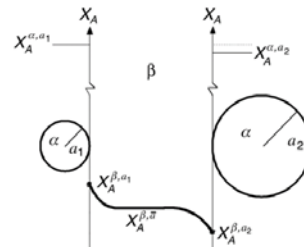
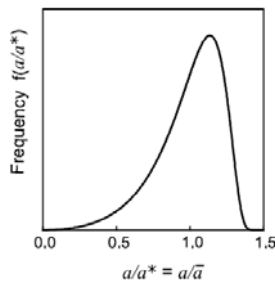
- Basic Assumptions: (i) infinitely dispersed system (meaning?)
- (ii) constant interface mobility (meaning?)

Diffusion-controlled GG (by LSW)

Interaction btw. average-sized grain and an individual grain

$$\frac{da}{dt} = -\frac{D(C_a - C_{\bar{a}})}{a} \quad \frac{da}{dt} = \frac{2D\gamma C_\infty V_m}{RTa} \left(\frac{1}{\bar{a}} - \frac{1}{a} \right)$$

$$\bar{a}_t^3 - \bar{a}_0^3 = \frac{8D\gamma C_\infty V_m}{9RT} t$$



Lifshitz and Slyozov, *J. Phys. Chem. Solids*, **19**, 35 (1961).
Wagner, *Z. Electrochem.*, **65**, 581 (1961).

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Lifshitz-Slyozov-Wagner (LSW) Theory

Basic Assumptions: (i) infinitely dispersed system (meaning?)
 (ii) constant interface mobility (meaning?)

Interface Reaction-controlled GG (by Wagner)

Interaction btw. average-sized grain and an individual grain

$$\frac{da}{dt} = K(C_{\bar{a}} - C_a) = \frac{2K\gamma C_{\infty} V_m}{RT} \left(\frac{1}{\bar{a}} - \frac{1}{a} \right)$$

$$\bar{a}_t^2 - \bar{a}_0^2 = \frac{64 K \gamma C_{\infty} V_m}{81 RT} t \quad \text{(This Eq. is similar to that of NGG for a single phase system)}$$

Physically Wrong!

Wagner, *Z. Electrochem.*, **65**, 581 (1961).

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Lifshitz-Slyozov-Wagner (LSW) Theory

Basic Assumptions: (i) infinitely dispersed system (meaning?)
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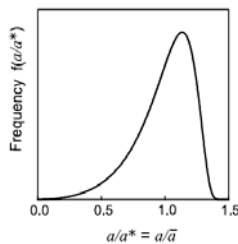
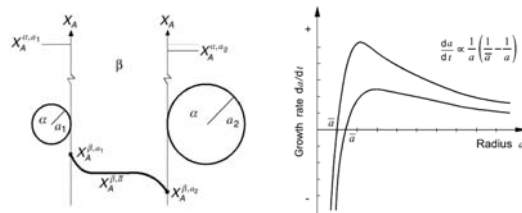
Diffusion-controlled GG (by LSW)

Interaction btw. average-sized grain and an individual grain

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$$\bar{a}_t^3 - \bar{a}_0^3 = \frac{8 D \gamma C_{\infty} V_m}{9 RT} t$$



Interface Reaction-controlled GG (by Wagner)

$$\frac{da}{dt} = K(C_{\bar{a}} - C_a) = \frac{2K\gamma C_{\infty} V_m}{RT} \left(\frac{1}{\bar{a}} - \frac{1}{a} \right) \quad \text{Physically Wrong!}$$

$$\bar{a}_t^2 - \bar{a}_0^2 = \frac{64 K \gamma C_{\infty} V_m}{81 RT} t \quad \text{(This Eq. is similar to that of NGG for a single phase system)}$$

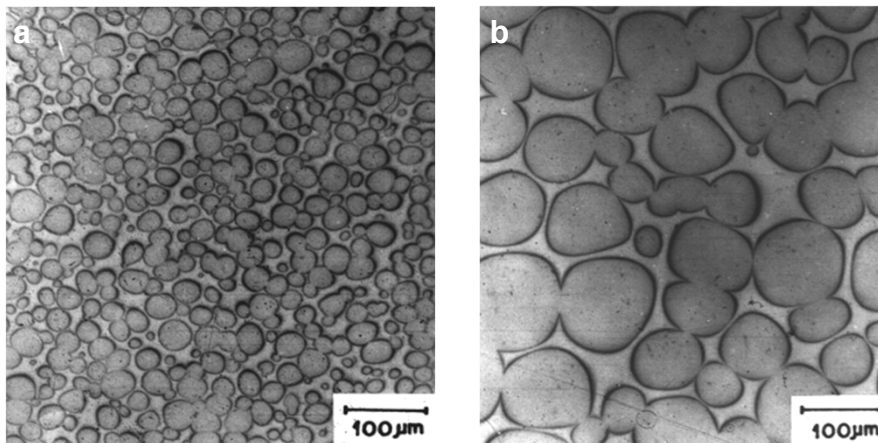
Lifshitz and Slyozov, *J. Phys. Chem. Solids*, **19**, 35 (1961).

Wagner, *Z. Electrochem.*, **65**, 581 (1961).

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Normal Grain Growth

Stationary Grain Growth

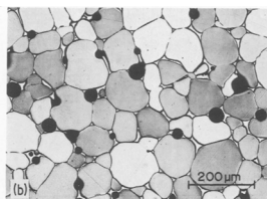


Microstructure of 70W-30Ni alloy annealed at 1540°C for (a) 30 min. and (b) 15 h.

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Effect of inert particles on GG kinetics

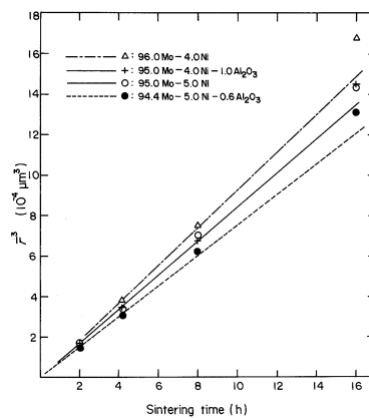
Normal Grain Growth



95Mo-4Ni-1Al₂O₃



Figure 4 Typical etch boundaries within growing molybdenum grains in contact with Al₂O₃ particles in a 94.4Mo-5Ni-0.6Al₂O₃ alloy cyclically sintered at 1460°C with four holding times (1 + 1 + 1 + 1 h).



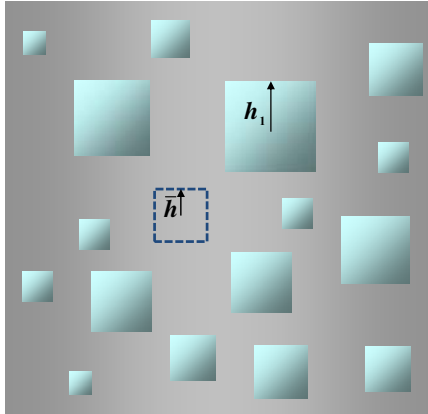
- The grain growth inhibition by inert particles is limited to the vicinity of the region in contact with the particles
- The effect of inert particles is marginal.

Kang and Yoon, *J. Mater. Sci.*, **20**, 3213 (1985).

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Fundamentals of Grain Growth in a Matrix

Ostwald ripening: Result of growth/dissolution of individual grains



Interaction of an individual grain with a critical sized grain

$$\Delta g \propto \left(\frac{1}{h} - \frac{1}{h_1} \right) \gamma_{sl}$$

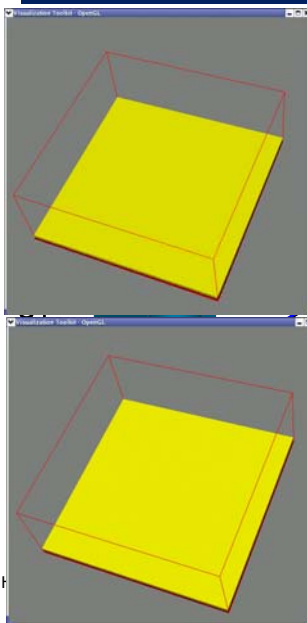


(Difference in Capillary Pressure)

Growth and dissolution of single crystal grains in a liquid matrix

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Crystal Growth in a Matrix



Processes of diffusion and interface reaction

Diffusion

Growth Rate of a Faceted Crystal, v_R

Driving Force, Δg

Effective Rate

$$v = \frac{v_D v_R}{v_D + v_R}$$

Progress in material science, vol. 11. Oxford, UK: Pergamon Press; 1963. p. 77.

Abbaschian, Metall. Trans. A., 22A, 1271 (1991).

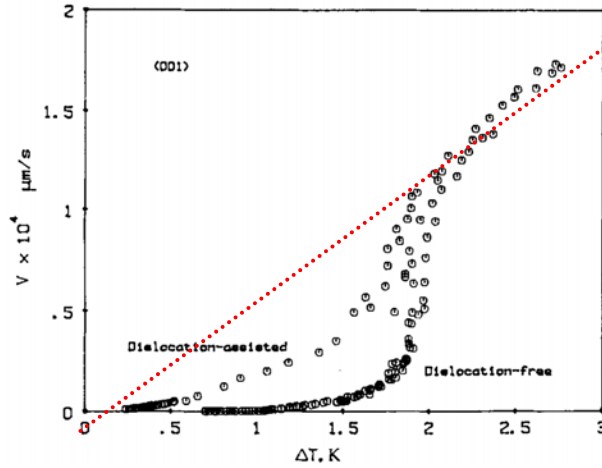
... et al., J. Mater. Res., 24, 2949 (2009).

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Nonlinear Migration of Faceted Sol./Liq. Interface

Experimental Observation

(001) Ga Single Crystal

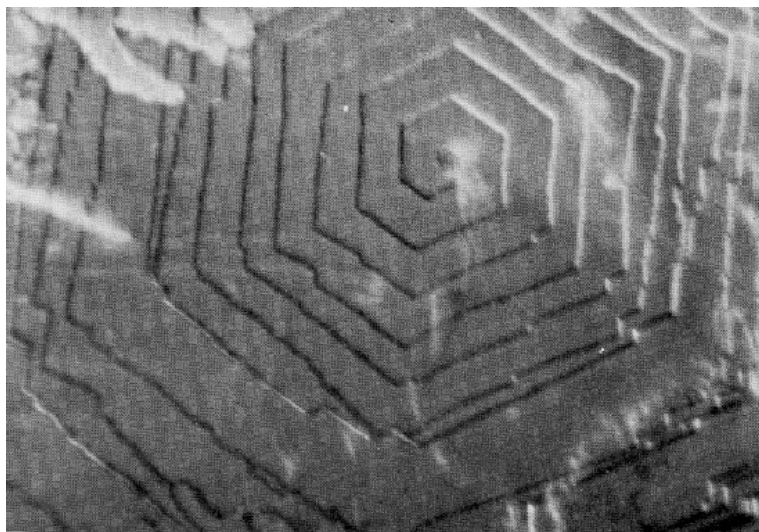


S.D. Peteves and R. Abbaschian, *Metall. Trans. A*, **22** [6], 1259 (1991).

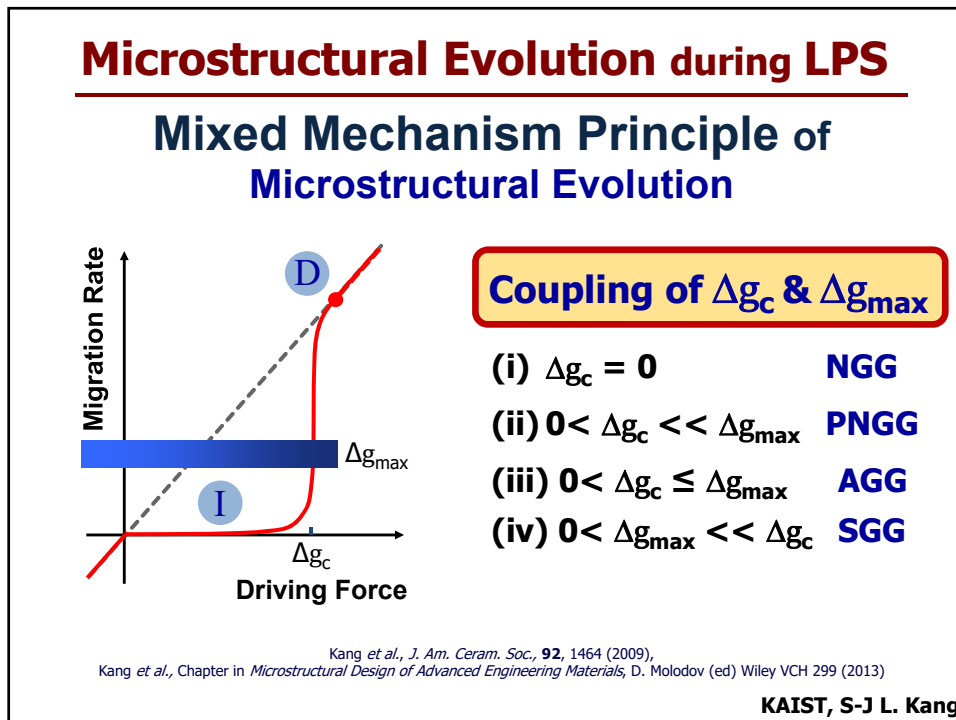
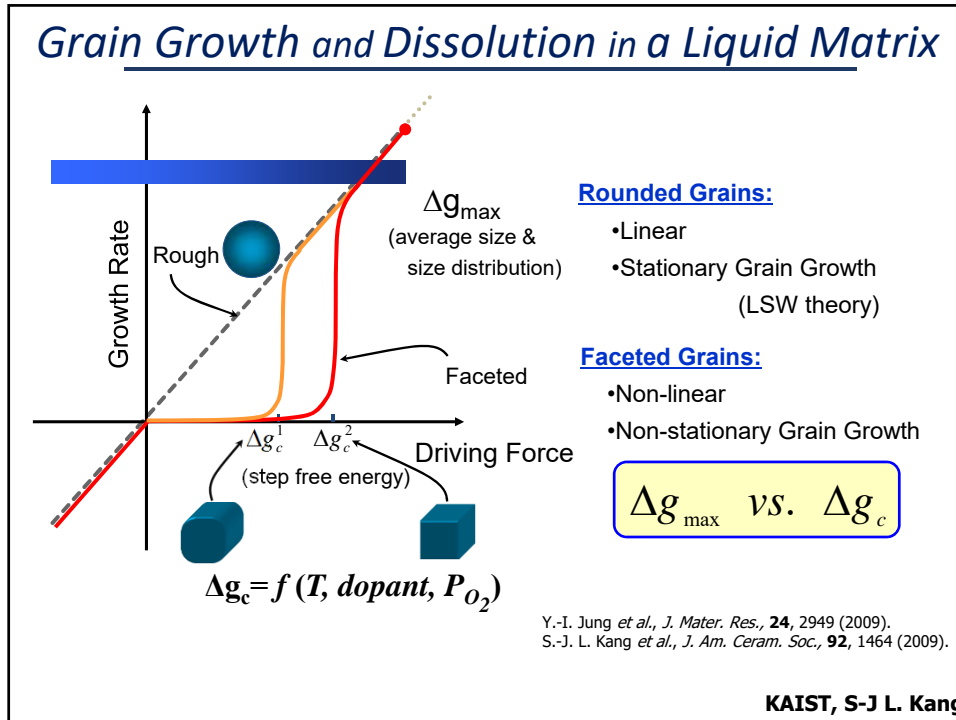
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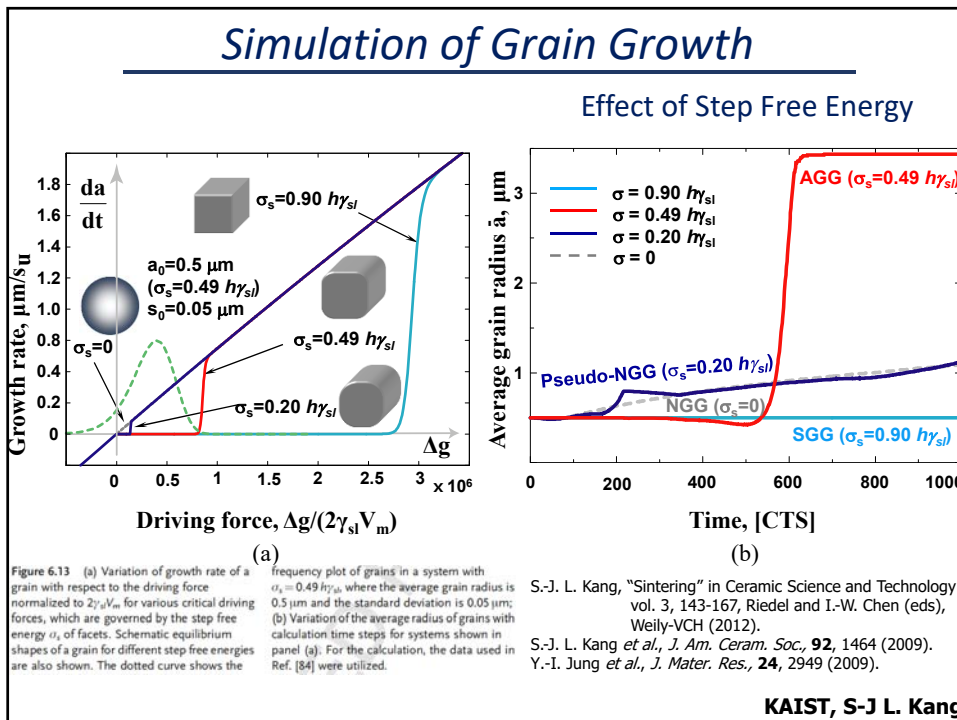
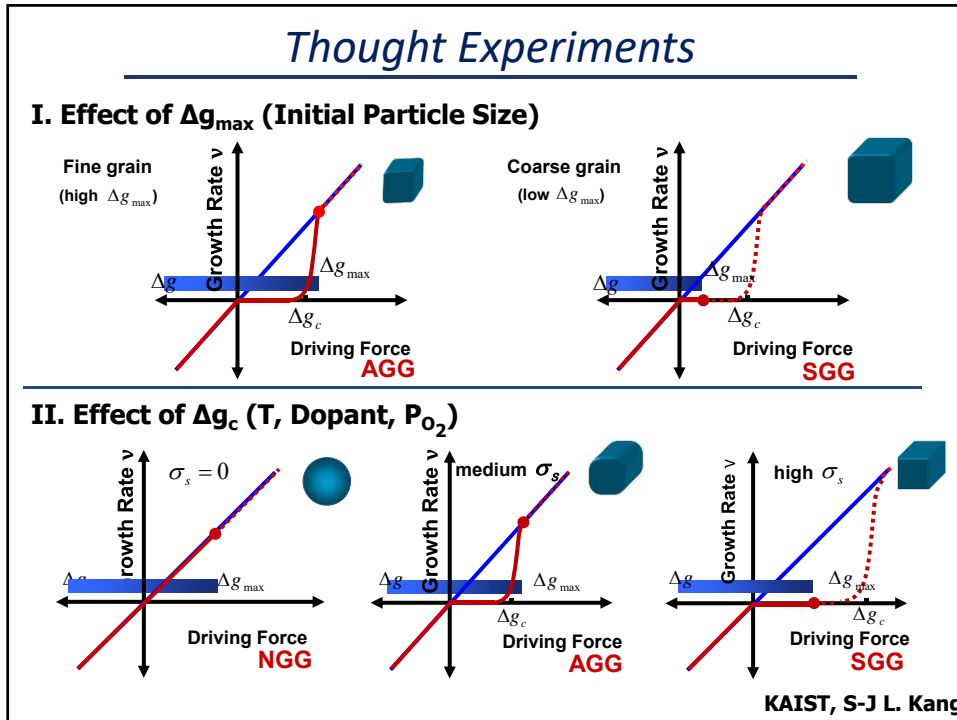
Defect-assisted Growth of a Crystal in a Matrix

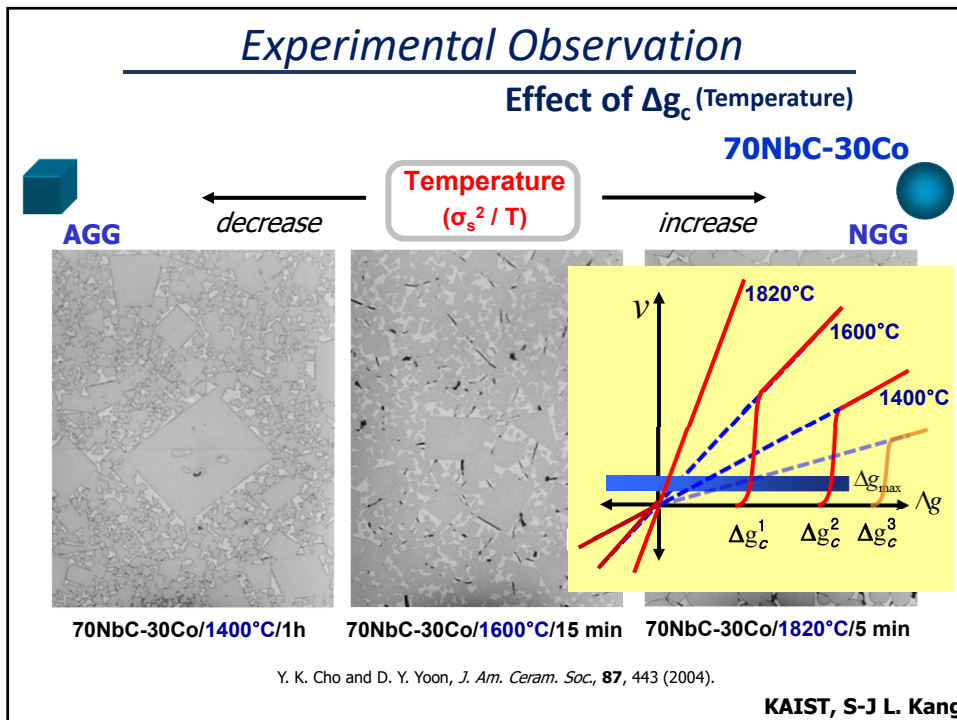
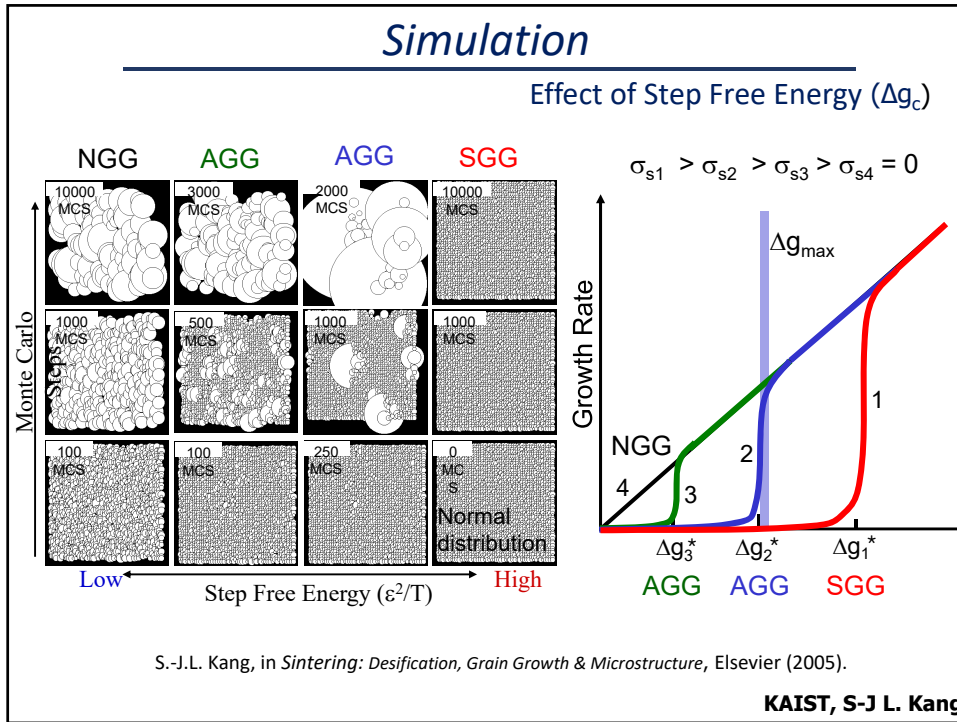
Growth spiral on CdI crystals growing from water solution (by Jackson)

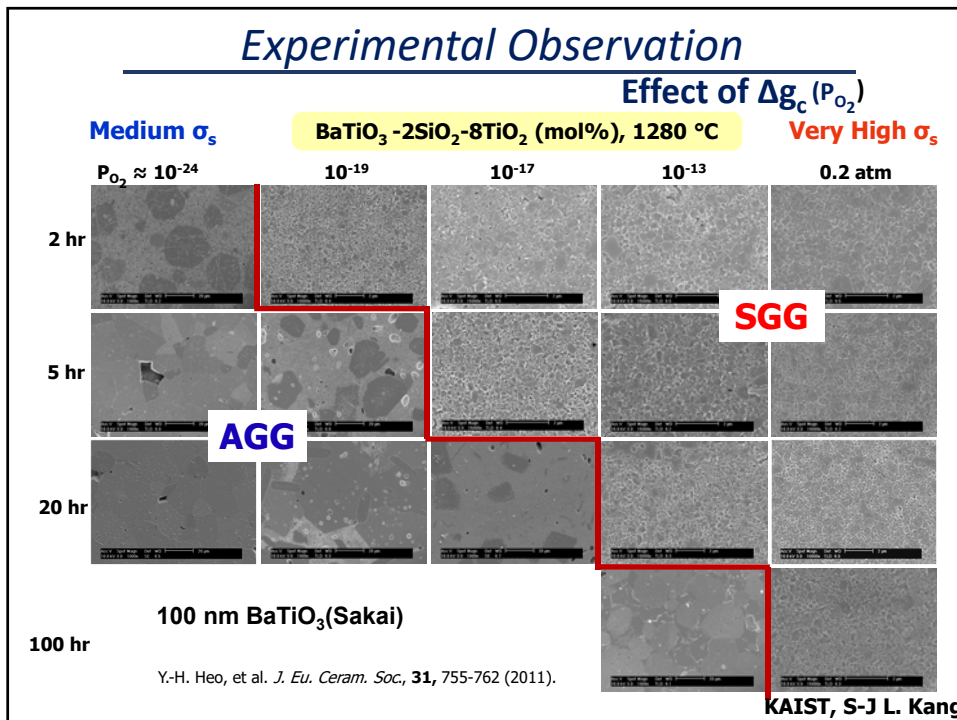
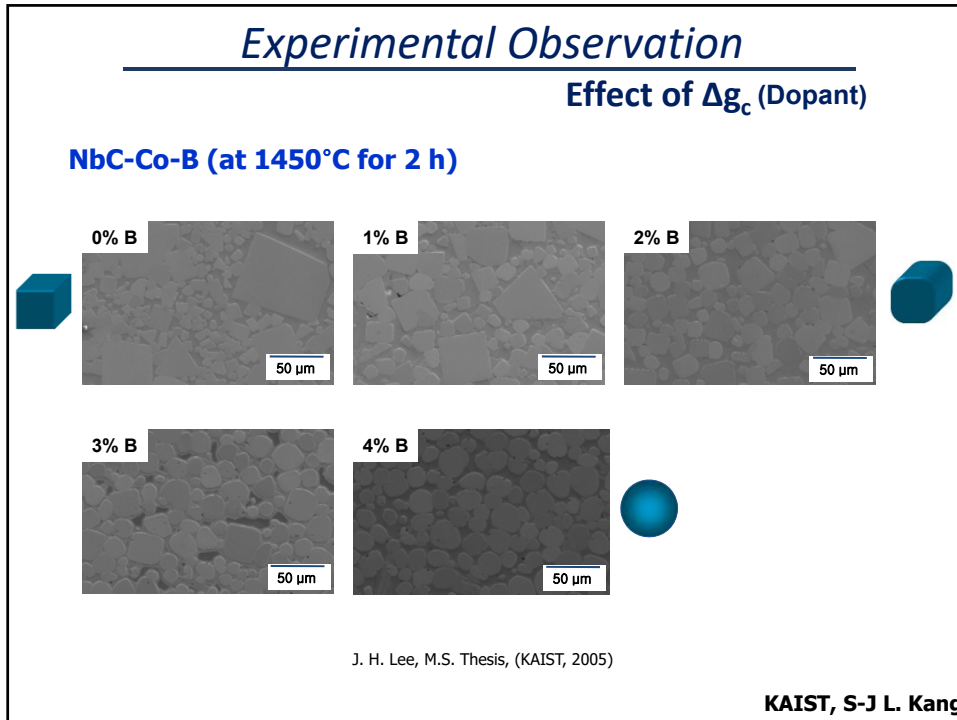


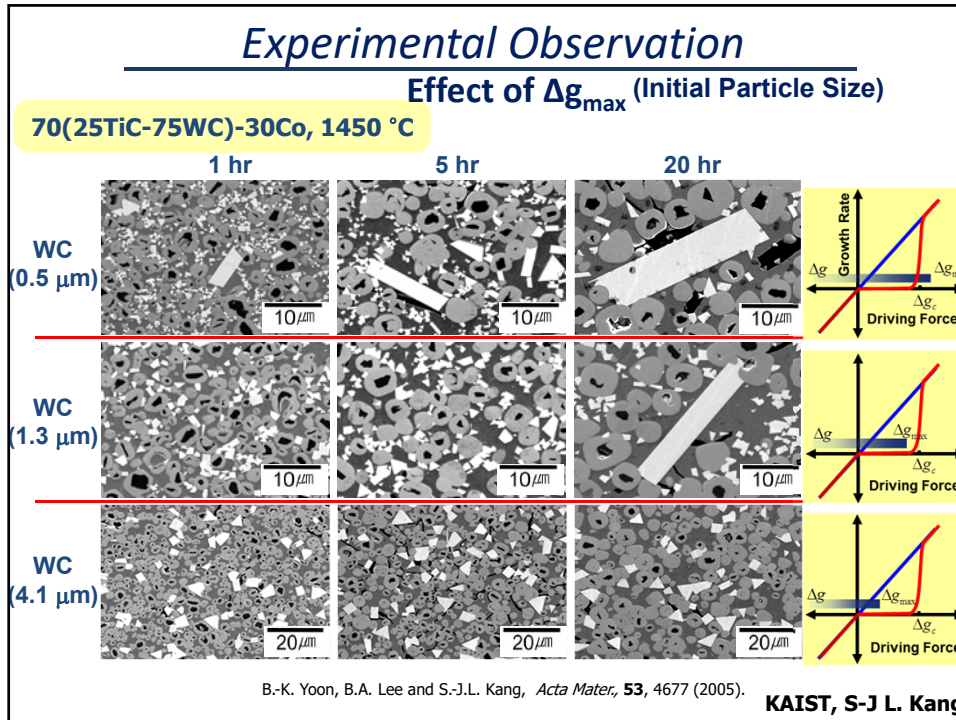
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Experimental Supports for the Principle

Experimental Observations and Interpretations (Two-Phase Systems)

• Effect of Δg_c (T, Dopant, P_{O_2})

- Sialon, Si_3N_4 (Kang and Han, 1995)
- SrTiO_3 (Chung *et al.*, 2002 (Dopant, P_{O_2}))
- NBT-BT (Moon and Kang, 2008)
- BaTiO_3 (Chang and Kang, 2009)
- NBT-BT (Moon *et al.*, 2011 (Dopant))
- NbC-Co (Cho and Yoon, 2004 (T))
- NbC-Fe (Oh *et al.*, 2000 (Dopant))
- PMN-PT (Wallace *et al.*, 2002 (Dopant))
- SiC (Jang *et al.*, 1996 (P_{O_2}))
- PMN-PT (Kim *et al.*, 2006, (Dopant, T))
- KNN (Fisher *et al.*, 2009)
- BaTiO_3 (Heo *et al.*, 2011 (P_{O_2}))
- Alumina (Park *et al.*, 2002 (Dopant))
- NbC-Co (Lee and Yoon, 2005 (Dopant))
- (Nb,Ti)C-Co (Choi *et al.*, 2002 (Dopant))
- WC-Co (Lee *et al.*, 2003 (Dopant))
- SrTiO_3 (Sano *et al.*, 2007) etc.

• Effect of Δg_{\max}

- BaTiO_3 (Jung *et al.*, 2003)
- WC-Co (Park *et al.*, 1996)
- TiC-WC-Co (Yoon *et al.*, 2005)

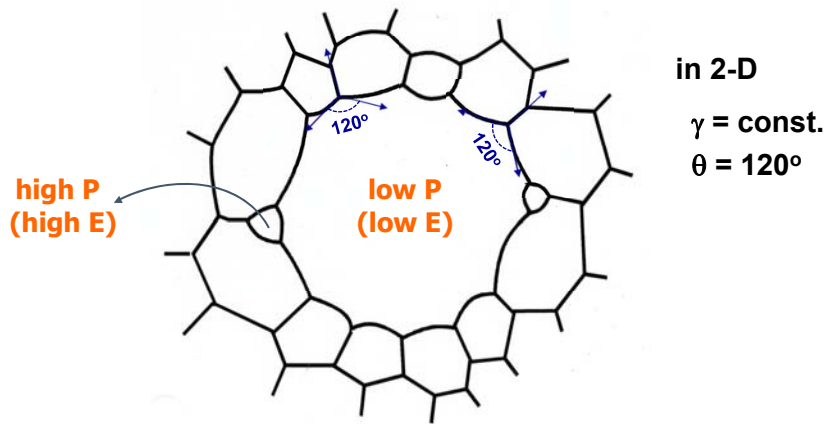
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Chap. Solid State Sintering

GG: Increase in average grain size

Result of boundary migration

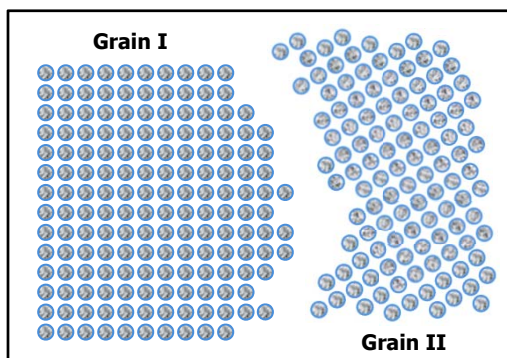
Driving Force



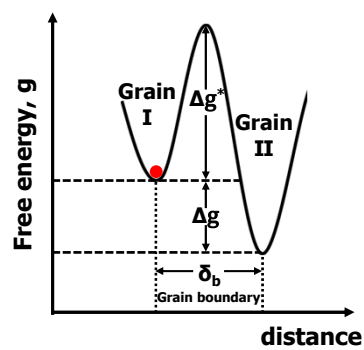
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Atomic Motion in Boundary Migration

$$\Delta g \text{ (Capillary energy)} = (2\gamma_b/r) V_m$$



Random jump of atoms across the boundary



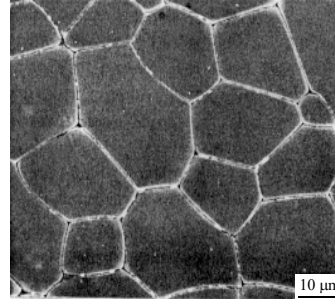
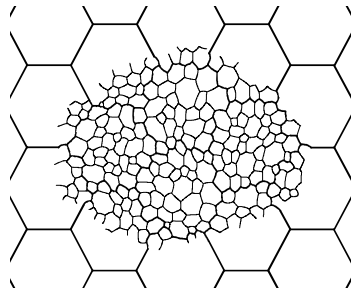
Diffusion Control :

$$M_b = \frac{D_b^\perp}{RT} \propto \exp\left(-\frac{\Delta g^*}{RT}\right)$$

Kang et al., *J. Ceram. Soc. Jpn.*, 124, 259 (2016).

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Driving Force for Grain Growth



Etched and polished section of Al_2O_3

Driving Force for the Growth of a Grain

$$\Delta g = 4\gamma_b \left(\frac{1}{\bar{G}} - \frac{1}{G} \right) \propto \left(\frac{1}{\bar{G}} - \frac{1}{G} \right)$$

The mean field concept is adopted.

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GG in Pure Materials

The Boundary mobility is assumed to be constant irrespective of the driving force.

$$\text{Mobility} = \text{const.} \neq f(F_b)$$

The boundary energy is also assumed to be constant, $\gamma_b = \text{constant}$

$$\begin{aligned} \frac{d\bar{G}}{dt} &= \alpha \bar{v}_b = \alpha J \Omega \\ &= \alpha \frac{D_b^\perp}{kT} (\nabla P) \Omega \\ &= \alpha \frac{D_b^\perp}{RT} \frac{2\gamma_b}{\bar{R}_o} \frac{V_m}{\omega} \end{aligned}$$

$$\begin{aligned} \frac{d\bar{G}}{dt} &= \frac{D_b^\perp 2\gamma_b V_m}{\beta RT \bar{G} \omega} \\ \bar{G}_t^2 - \bar{G}_{t_0}^2 &= \frac{4D_b^\perp \gamma_b V_m}{\beta RT \omega} t \\ &\text{Parabolic law or} \\ &\text{Square law} \end{aligned}$$

For an individual grain,

$$\frac{dG}{dt} = M_b \left[4\gamma_b \left(\frac{1}{\bar{G}} - \frac{1}{G} \right) / \omega \right] V_m$$

Normal Grain growth:
Invariable distribution of
relative grain size
(stationary GG)

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Some Considerations on Grain Growth

- Grain growth in terms of topology

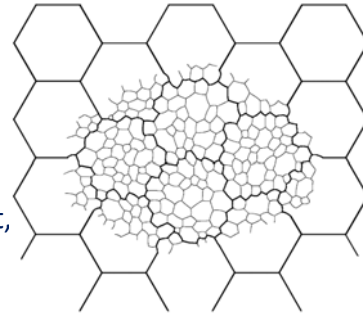
From $C - E + P = 1$,

$$\sum (6 - n)P_n + h_o - h_i = 6$$

- von Neumann equation

For a 2-dim. system where M is constant,

$$\frac{dA}{dt} = \frac{\pi M \gamma_b}{3} (n - 6)$$



- Deviation from NG behavior due to

- (i) $\gamma_b M_b \neq \text{const.}$
- (ii) Presence of 2nd phase particles $M_b = \text{constant}$
- (iii) Solute segregation $\neq f(\Delta g) \rightarrow \text{AGG}(X)$
- (iv) Non-constant mobility of the boundary

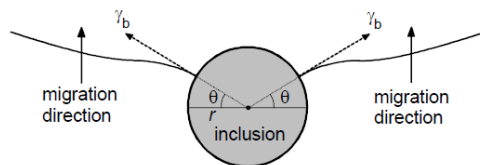
$M_b = f(\Delta g)$: This condition is related to the boundary structure

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Effect of 2nd Phase Particles

Smith-Zener Effect

Qn: What is the thermodynamic basis of the Smith-Zener effect?



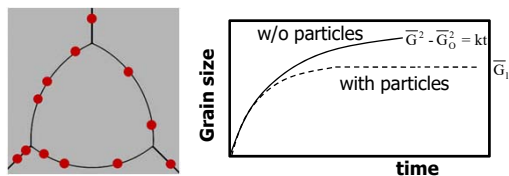
For uniform distribution of second phase particles

$$F_d = \gamma_b \sin \theta \times 2\pi r \cos \theta = \pi r \gamma_b \sin 2\theta$$

$$F_d^\sigma = \frac{3f_v \gamma_b}{2r}$$

$$\frac{d\bar{G}}{dt} = \frac{D_b^\dagger}{RT} \frac{1}{\omega} \left[2\gamma_b \frac{V_m}{\beta \bar{G}} - \frac{3f_v \gamma_b V_m}{2r} \right]$$

$$\bar{G}_l = \frac{4r}{3f_v \beta} \quad \text{or} \quad \bar{R}_l = \frac{2r}{3f_v \beta}$$



Qn: Ostwald ripening of particles? In reality, such a high drag?

Addition of BT particles to Ni powder in fabrication of MLCC: an application example of Zener drag

Smith CS. AIME, 175, 15 (1949). Manohar PA, et al., ISIJ Inter., 38, 913 (1998).

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Effect of solute segregation

Solute/Impurity segregation

Qn: Why solutes segregate at the grain boundary?

- Solute Segregation at GB
- Many models and theories of GB segregation.
- The simplest one is McLean's model that assumes mono-layer segregation of a single adsorbate without interference btw solvent and solute atoms (no site-to-site interaction, cf: *regular solution model*).

$$\frac{X_B^b}{X_A^b} = \frac{X_B}{X_A} \exp\left(\frac{-\Delta E}{kT}\right)$$

Derived by use of (i) statistical thermodynamics or
(ii) the mass action law

ΔE : free energy of segregation

Qn: What can be the factors that affect solute segregation?

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Effect of solute segregation

Solute/Impurity drag

Qn: Drag force of the segregated solutes against the boundary migration?

Qn: The difference btw the Smith-Zener drag and the solute drag?

Derivation of the drag force

(i) calculation of $C(x)$ from eq. $D \frac{\partial C}{\partial x} + \frac{DC}{kT} \frac{\partial E}{\partial x} + v_b(C - C_\infty) = 0$

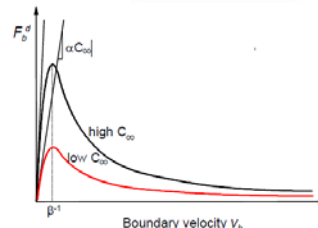
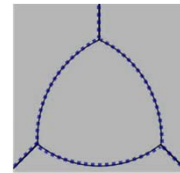
(ii) calculation of the net drag force

$$F_b^d = - \int_{-\infty}^{\infty} n(x) \frac{dE}{dx} dx$$

$$= -N_v \int_{-\infty}^{\infty} [C(x) - C(\infty)] \frac{dE}{dx} dx$$

An approximated solution: $F_b^d = \frac{\alpha C_\infty v_b}{1 + \beta^2 v_b^2}$

- α : the drag force per unit concentration of solute and per unit velocity of moving boundary when $\beta^2 v_b^2 \ll 1$.
- β : the time required for solute atoms to diffuse one unit distance. (the inverse of the drift velocity)



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Effect of solute segregation

Boundary migration

$$F_b^t = F_b^o + F_b^d = \frac{v_b}{M_b^o} + \frac{\alpha C_\infty v_b}{1 + \beta^2 v_b^2} = v_b \left(\frac{1}{M_b^o} + \frac{\alpha C_\infty}{1 + \beta^2 v_b^2} \right)$$

Boundary velocity, v_b

Velocity
w/o segregation
with segregation
Force

Two extreme cases

$$v_b \ll \beta^{-1} \quad v_b = \frac{F_b^t}{(1/M_b^o) + \alpha C_\infty} \approx \frac{1}{\alpha C_\infty} F_b^t$$

$$v_b \gg \beta^{-1} \quad v_b \approx M_b^o F_b^t$$

Qn: Boundary mobility in McLean model?
Drag = $f(\text{segregation, diffusivity})$

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Microstructure Development

in porous materials

Qn: What are the potential parameters that affect the trajectory of microstructural evolution?

A few points of consideration:

- Densification is governed by driving force (pore size) and densification mechanism.
Pore size varies with grain size.
- Grain growth is affected by grain size (driving force) and boundary migration mechanism.
Boundary control vs. Pore control (pore migration mechanisms)
- Location of pores
4-grain corner, 3-grain edge, 2-grain boundary

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Mobility of an Isolated Pore

$$v_p = M_p F_p$$

$$F_p dx \approx F_a \frac{\pi r^2 dx}{\Omega} 2r$$

$$(F_p)_{\max} = \pi \gamma \gamma_b$$

Zener drag

Figure II.I. Possible mechanisms of pore migration with a grain boundary.

Migration mechanism	Mobility, M_p
Surface diffusion	$M_p^s = \frac{D_s \delta_s \Omega}{\pi r^4 k T} \propto \frac{1}{r^4}$
Lattice diffusion	$M_p^l = \frac{D_l \Omega}{\pi r^3 k T} \propto \frac{1}{r^3}$
Gas diffusion	$M_p^g = \frac{D_g p_\infty \Omega^2}{2 \pi r^3 (k T)^2} \propto \frac{1}{r^3}$
Evaporation/condensation	$M_p^{e/c} = \frac{p_\infty \Omega^2}{\sqrt{2} m r^2} \left(\frac{1}{\pi k T} \right)^{3/2} \propto \frac{1}{r^2}$

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Pore Migration and Grain Growth

Qn: (i) move together, (ii) separated from the boundary

Boundary velocity in the presence of pores $v_b = M_b(F_b - NF_p)$

(i) Boundaries move together with pores

$$v_b = v_p = M_p F_p = M_b(F_b - NF_p)$$

$$v_b = \frac{M_b}{1 + N(M_b/M_p)} F_b$$

(ii) Pores are separated from boundary

$$F_b > \left(\frac{M_p}{M_b} + N \right) F_p$$

For surface diffusion-controlled pore migration (boundary migration)

Brook, *J. Am. Ceram. Soc.*, **52**, 56 (1969).

Harmer, in *Structure and Properties of MgO and Al2O3 Ceramics*, W. D. Kingery (ed.), Am. Ceram. Soc. Inc., Columbus, 679 (1985)

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Densification and Grain Growth: Microstructure Development

Densification rate:

$$\frac{1}{\rho} \frac{d\rho}{dt} = \frac{K_1(1-\rho)^k}{G^m \rho}$$

Grain Growth rate:

$$\frac{1}{G} \frac{dG}{dt} = \frac{K_2}{G^n(1-\rho)^l}$$

• $\frac{d\rho}{dG} = \left(\frac{K_1}{K_2}\right) G^{n-m-1} (1-\rho)^{k+l}$

Densification	<i>m</i>	<i>k</i>
D_l	3	1/3
D_b	4	0
Grain Growth	<i>n</i>	<i>l</i>
D_s	4	4/3
Gas Diff.	3	1
Evap./Cond.	2	2/3
D_b^\perp	2	0

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Effect of Grain (Particle) Size

Examples

Densification : lattice diffusion
Grain Growth : surface diffusion

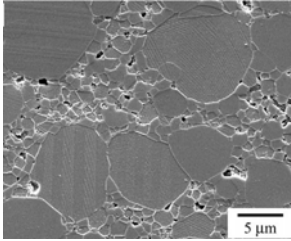
Densification : grain boundary diffusion
Grain Growth : evaporation/condensation

Relative densification and coarsening rates vs. grain size.

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Abnormal (Exaggerated) **GG**

An extreme type of Grain Growth



0.1 mol% TiO₂-excess BaTiO₃
at 1250 °C for 50 h

Bimodal size distribution of grains

- the result of fast growth of a few (some) grains
and essentially no growth of matrix grains

Observation of AGG in many different systems

- (i) highly pure systems
- (ii) highly impure systems
- (iii) systems with second phase particles
- (iv) systems with a liquid matrix

Phenomenological Description of AGG

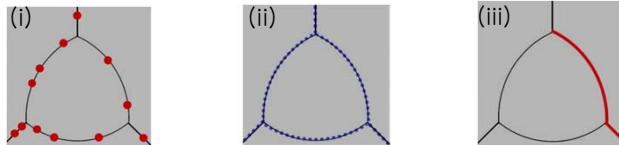
$$\frac{dG_a}{dt} = \frac{D_b^\dagger}{RT} \frac{2\gamma_b V_m}{\beta \bar{G}_m \omega} \quad \bar{G}_{a,t} - \bar{G}_{a,t_0} = \frac{2D_b^\dagger \gamma_b V_m}{\beta RT \bar{G}_m \omega} t$$

Consider the growth of a single crystal into a polycrystal
in a single/poly bilayer sample!

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Suggested Mechanisms of AGG

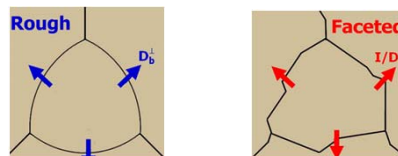
Early Mechanisms



- (i) Break-away of grain boundary from second phase particles (since 1950's)
- (ii) Break-away of grain boundary from segregated impurities (since 1960's)
- (iii) Uneven distribution of a second phase, in particular, a liquid (since 1970's)
"Complexion" hypothesis (since 2000's)
- (iv) Anisotropy in boundary mobility and boundary energy (simulation studies)

Recent Mechanism

- (v) Change in boundary migration mechanism with respect to the driving force



Kang *et al.*, *J. Am. Ceram. Soc.*, **92**, 1464 (2009).

Kang *et al.*, *J. Am. Ceram. Soc.*, **98**, 347 (2015).

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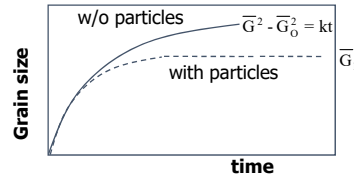
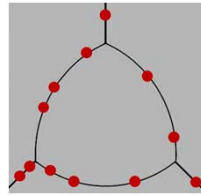
Early Mechanisms of AGG

The second phase particle(or pore) drag mechanism

• **Limit of grain growth** (Smith-Zener drag)

Smith CS. AIME 1949;175:15. Manohar PA, Ferry M, Chandra T. ISIJ Inter 1998;38:913.

2nd phase particles



• **Onset of AGG** : particle (pore)/bc

Brook RJ. J Am Ceram Soc 1969;52:56.
Rios PR. Acta Mater 1997;45:1785.

* Uneven distribution of particles or pores (local reduction or increase in pinning force)

- Valid only for two-phase systems with second phase particles or pores.
- AGG is observed only in some specific systems.
- AGG takes place also in highly porous materials with uniform pore distribution. (eg. BaTiO₃)

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Early Mechanisms of AGG

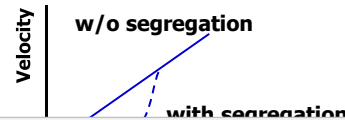
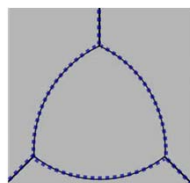
The solute drag mechanism

• **Grain Boundary Migration**

Cahn JW. Acta Metal 1962;10:789.
Lücke K. And Stüwe HP. On the theory of grain boundary motion, in Recovery and Recrystallization of Metal, L. Himmel (ed.) Gordon and Breach, New York, 171-210, 1962

Impurity Segregation and Boundary Migration

Segregation



• **Deviation from Normal Behavior**

Abbruzzese G, Buccioni M. Mater Sci Forum 2008;56:3739.
Kim SG, Park YB. Acta Mater 2008;56:3739.

- AGG is observed only in some specific systems.
- Not possible to explain SGG.
- Not possible to explain the increased tendency of AGG with decreasing particle size.
- Not possible to explain the variation of observed grain growth behavior with respect to the solute concentration in perovskite systems.

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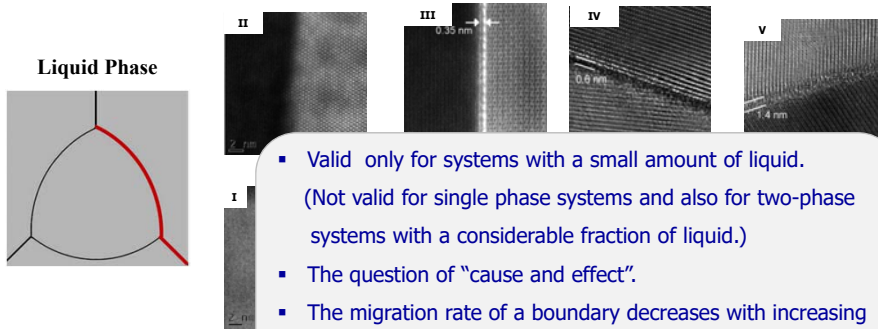
Early Mechanisms of AGG

The liquid film enhancement mechanism

(Highlighted as an introduction of several complexes)

• **Non-Uniform Distribution of Liquid**

Hennings DFK, Janssen R, Reynen PJL. J Amer Ceram Soc 1987;70:23.
 Hibbard GD et al., Scripta Mater 2002;47:83.
 Dillon SJ, Tang M, Carter WC, Harmer MP. Acta Mater 2007;55:6208. **(complexion)**



- Valid only for systems with a small amount of liquid. (Not valid for single phase systems and also for two-phase systems with a considerable fraction of liquid.)
- The question of "cause and effect".
- The migration rate of a boundary decreases with increasing solute segregation and liquid film formation

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Early Mechanisms of AGG

Effect of anisotropy in γ_b and M_b

$$v_b = M_b \cdot \gamma_b K$$

$M_b, \gamma_b = \text{const.} : \text{NGG}$

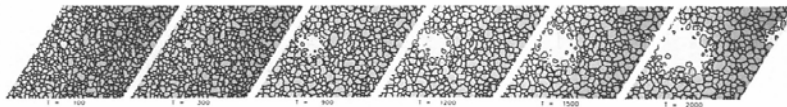
Anderson MP et al., Acta Metall., 1983;32:1127

$M_b, \gamma_b \neq \text{const.} : \text{Formation of AGs}$

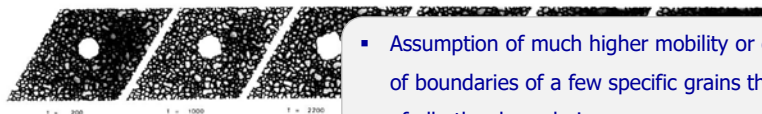
D. K. Lee et al., Scripta Mater, 2008;58:683
 Grest GS et al., Acta Metall., 1985;33:509

Rollett AD et al., Acta Metall., 1989;37:1127
 Hwang NM, J. Mater. Sci., 1998;33:5625

MC Simulation in a system with GB energy anisotropy (10 times)



MC Simulation in a system with GB mobility anisotropy (7.5 times)



- Assumption of much higher mobility or energy of boundaries of a few specific grains than that of all other boundaries.

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Common Feature in the Previous Models and Mechanisms

Diffusion-Controlled Boundary Migration

$$v_b = \frac{D_b^\perp}{RT} \cdot \nabla g \propto \exp\left(-\frac{\Delta g^*}{RT}\right) \cdot \Delta g$$

- (i) Particle (pore) drag : Reduction of Δg
- (ii) Impurity drag : Reduction of Δg
- (iii) Liquid Film : Change in Δg^* and δ_b
- (iv) Anisotropy of γ_b and M_b :
Change in Δg and Δg^*

Possibility of Interface Reaction- Controlled Boundary Migration ?

Kang et al., *J. Am. Ceram. Soc.*, **98** 347 (2015). KAIST, S-J L. Kang

Two Types of Grain Boundaries

Rough (atomically disordered)

Ti-excess BaTiO₃ in H₂

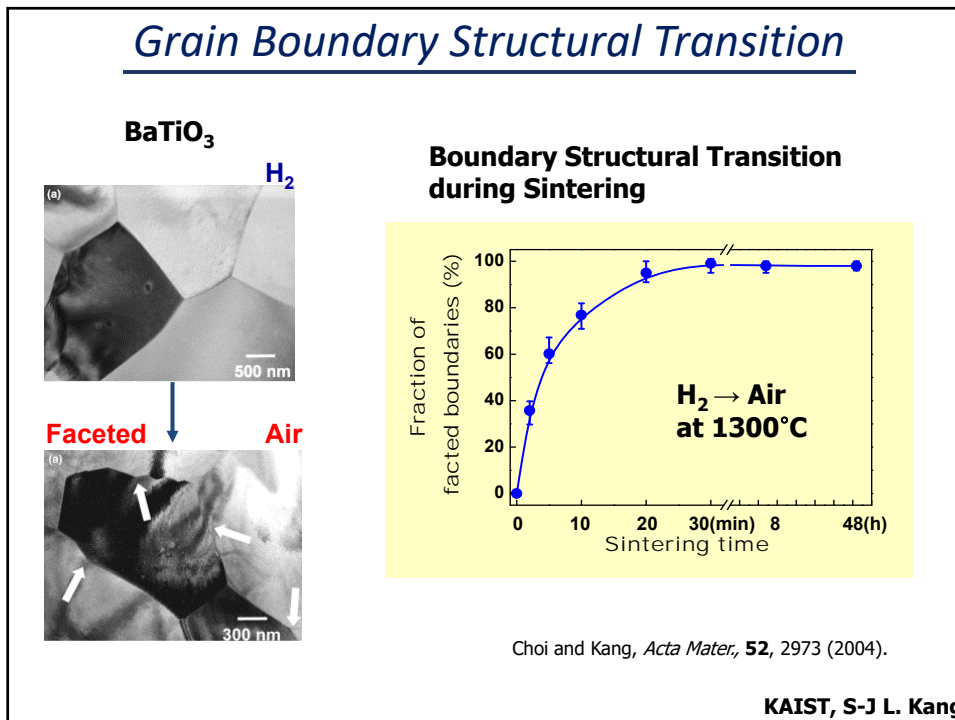
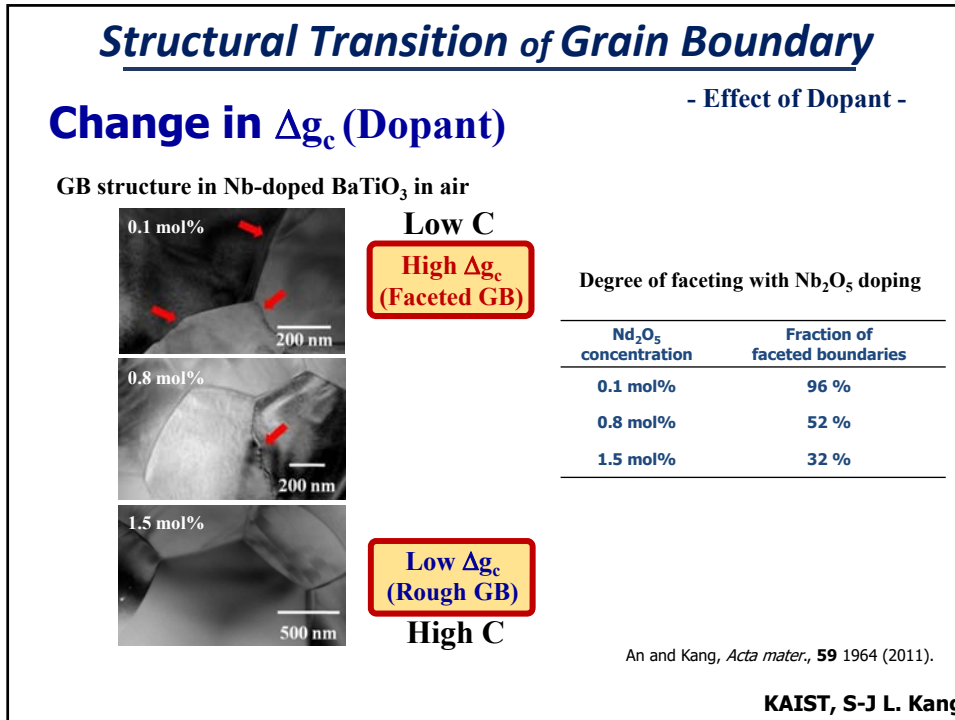
Faceted (atomically ordered)

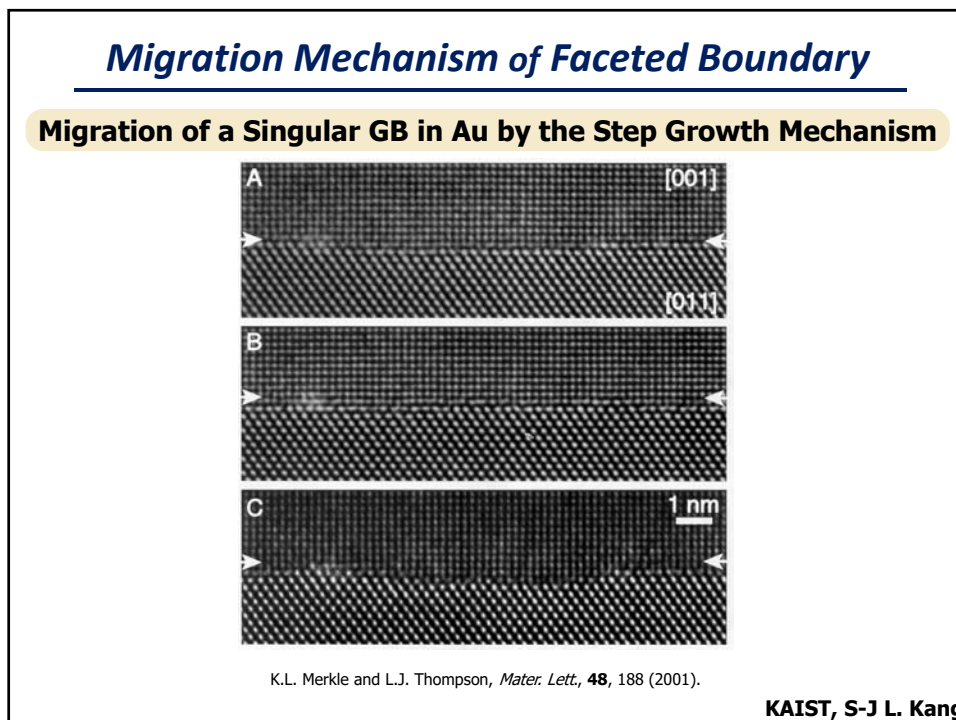
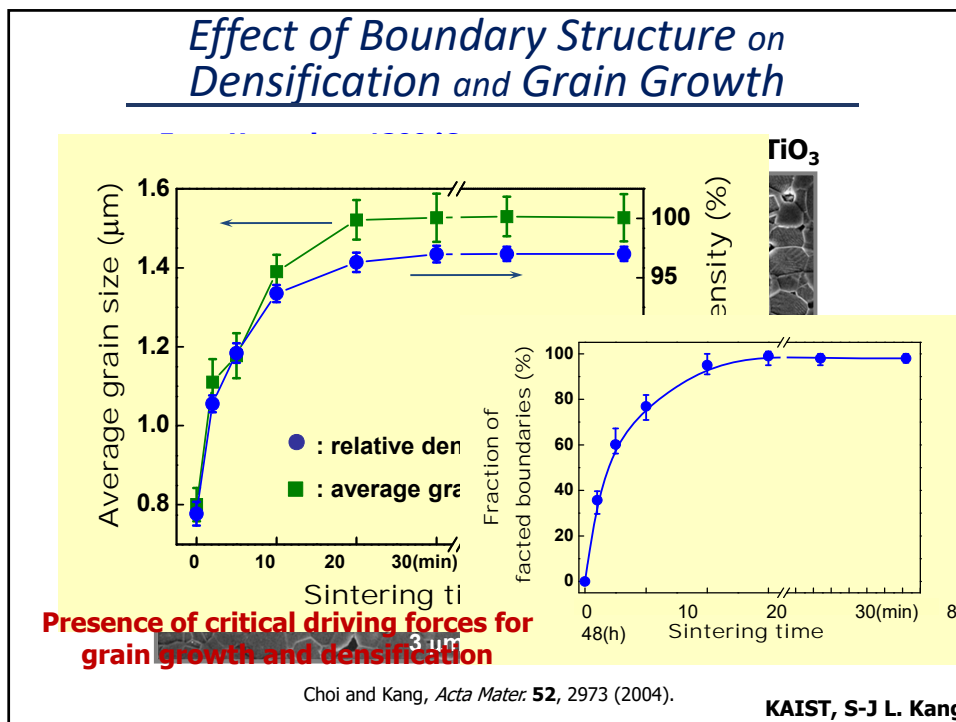
in air

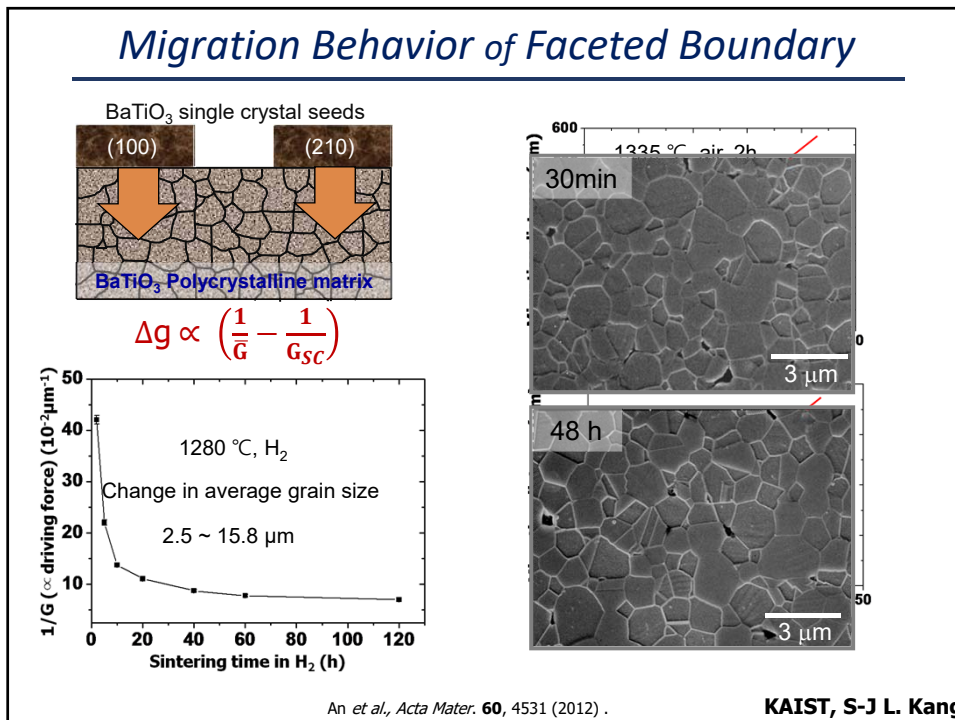
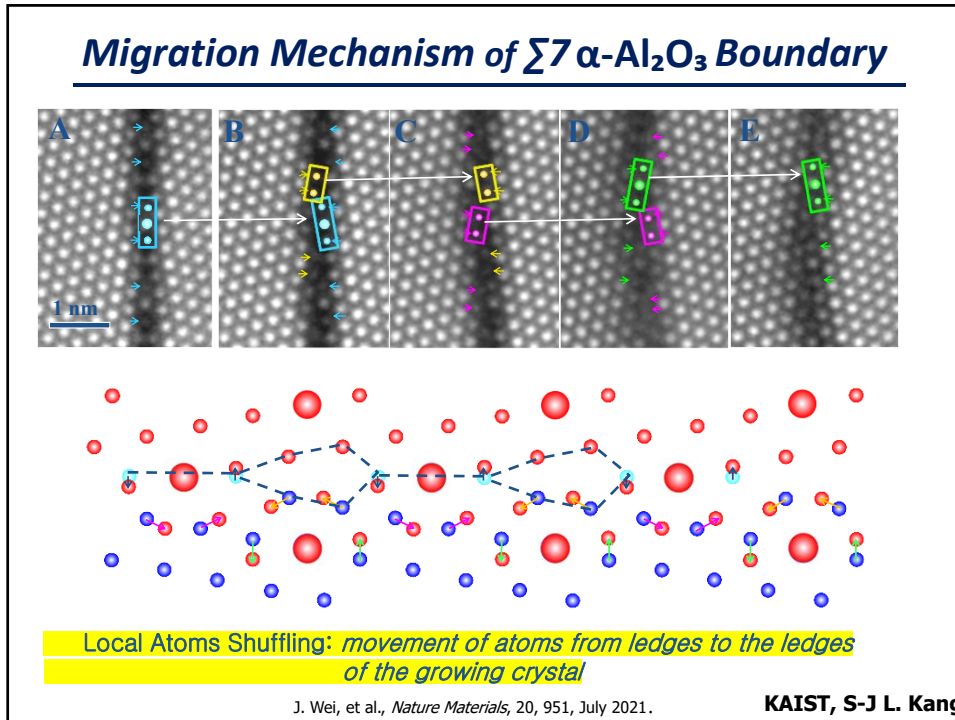
Variables: T, dopant, Po₂

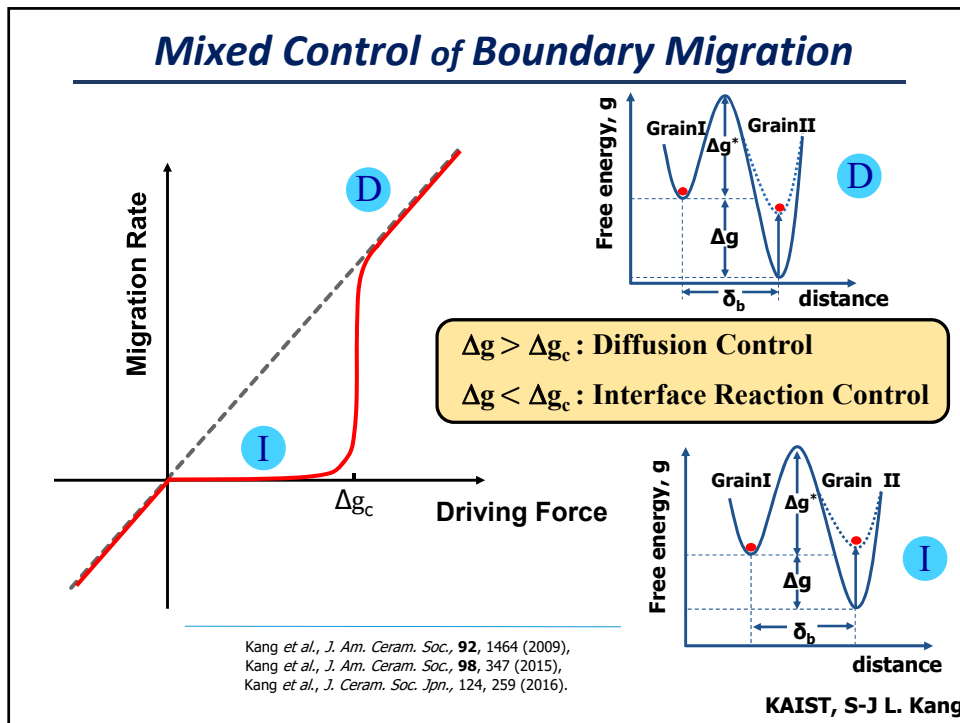
Choi and Kang, *Acta. Mater.* **52**, 2973 (2004).
S.-J. L. Kang, Chap.6, "Sintering" in *Ceramic Science and Technology*
(Ed : R. Riedel and I.-W. Chen) Wiley-VCH, 143-69 (2012).

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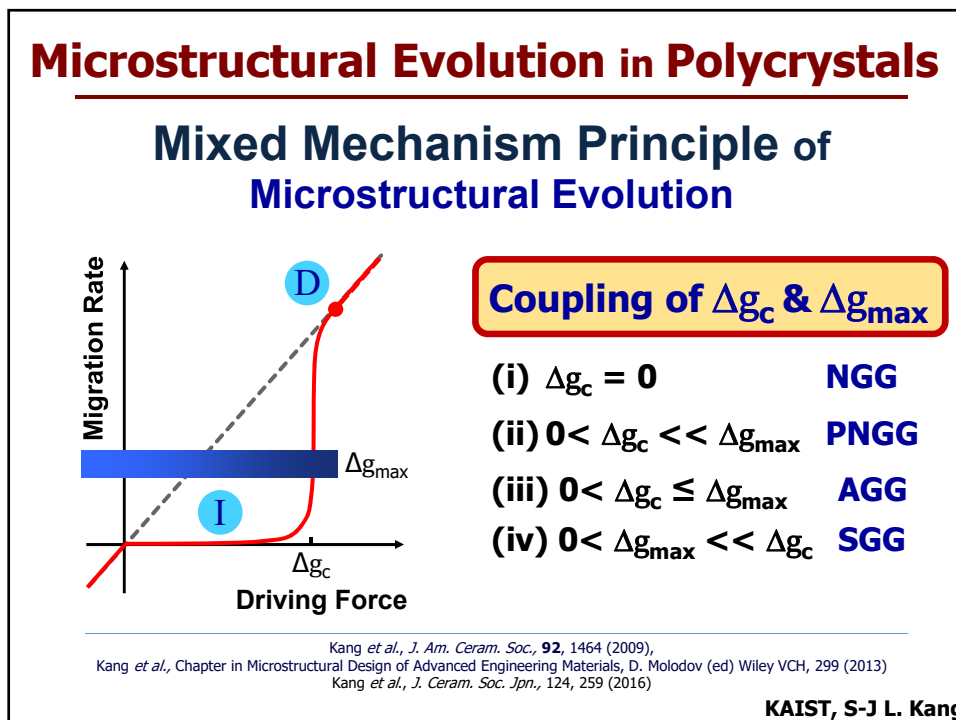
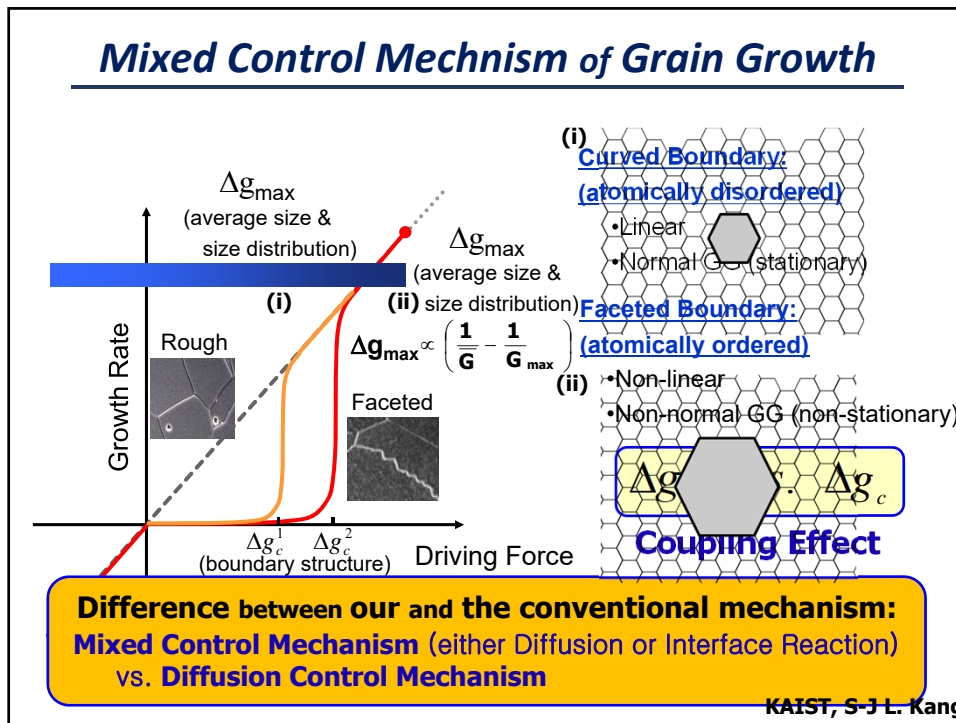


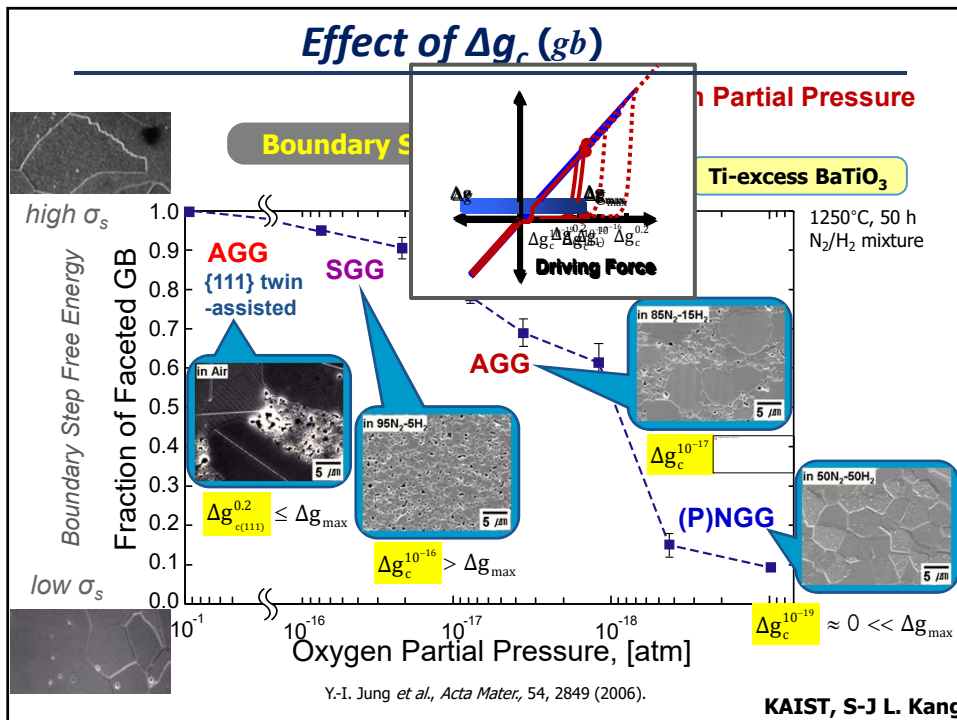
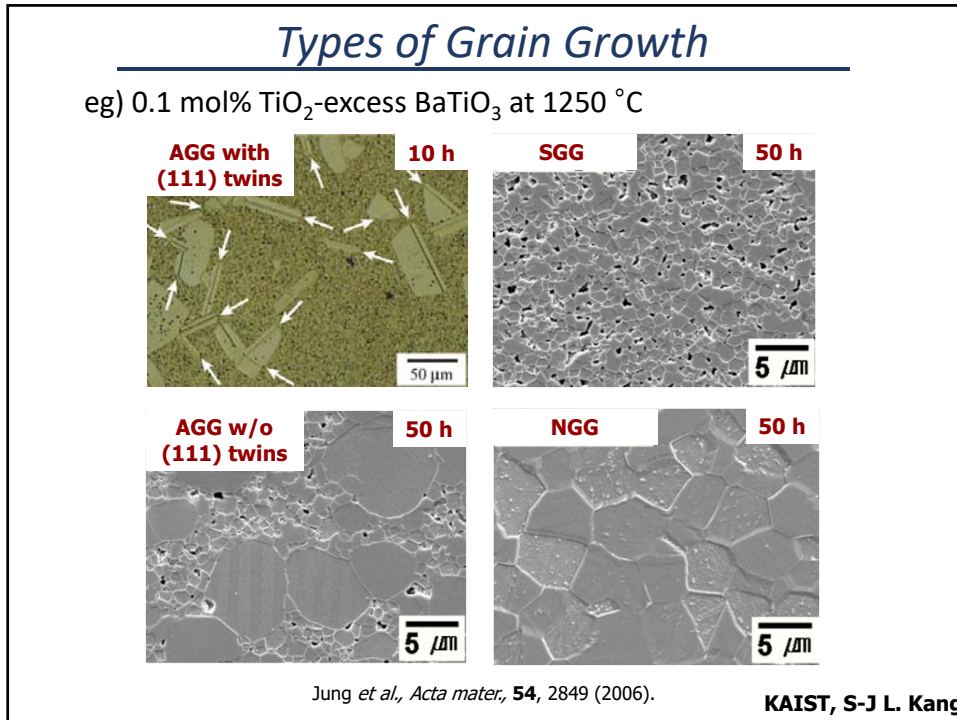


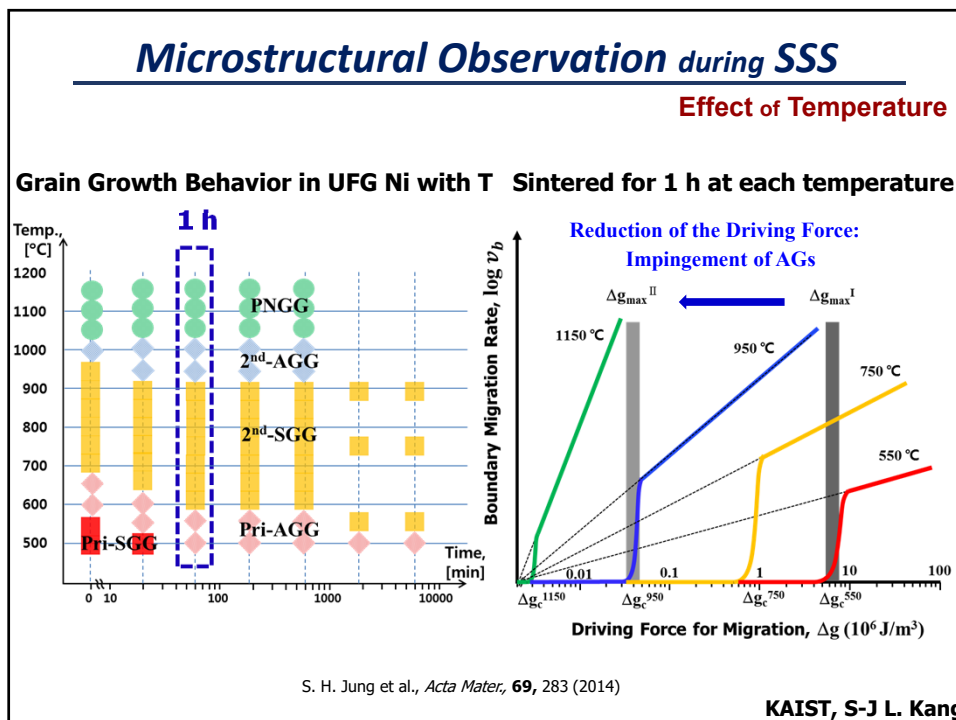
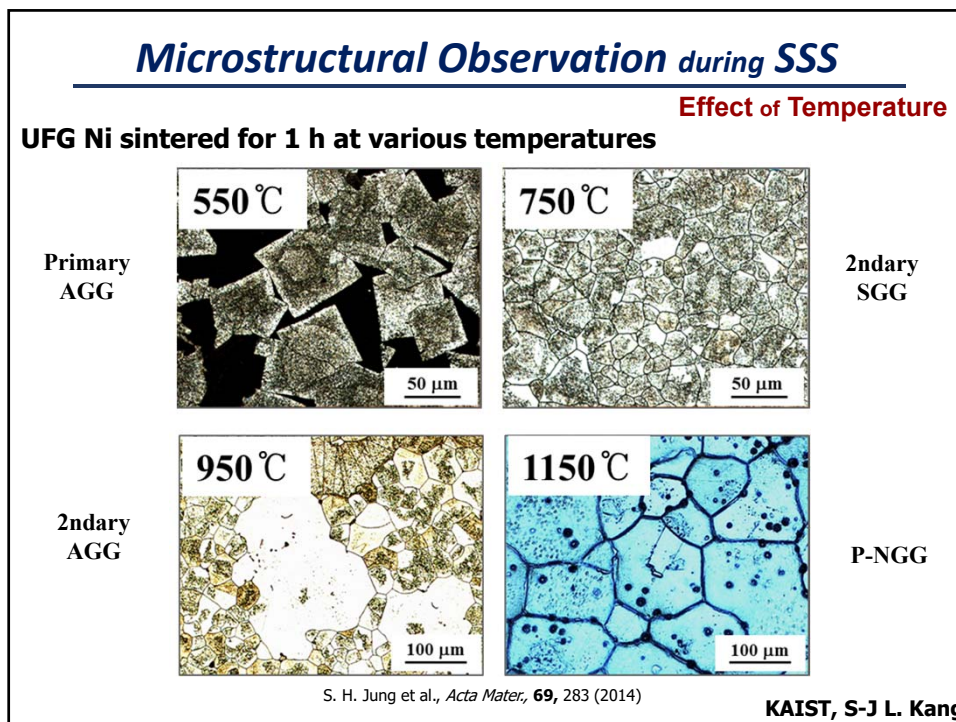
Summary of Recent Findings

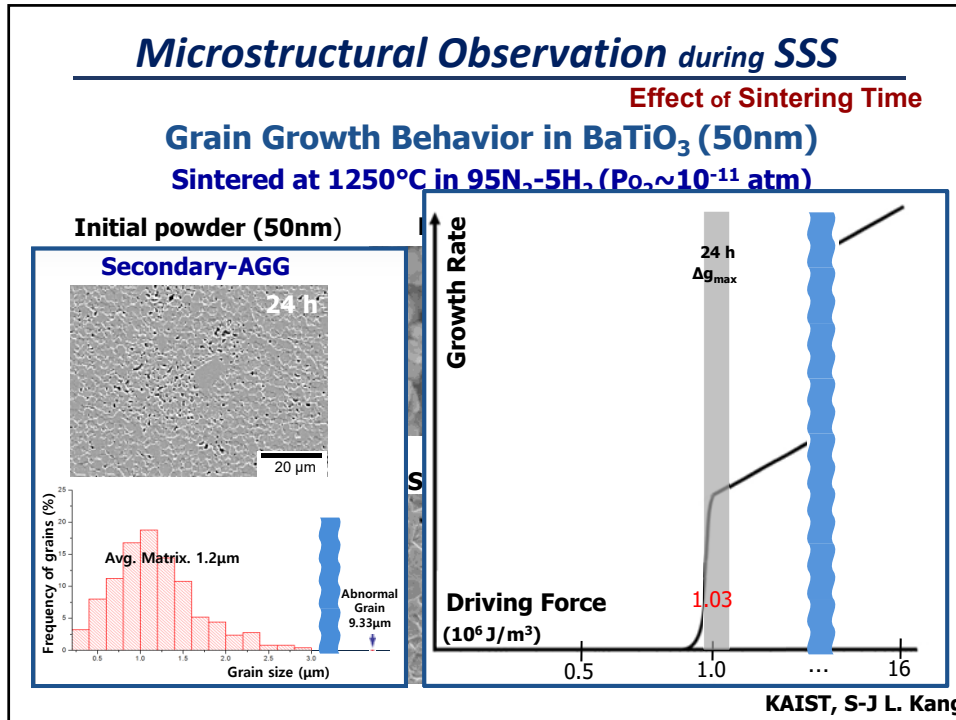
- **Migration mechanism of grain boundary**
 - is **not** dependent on
 - the presence of a liquid (film),
 - the presence of solutes, or
 - the presence of a 2nd phase (particles) at the boundary
 - but** dependent on
 - the morphology (atomic structure) of the grain boundary:
 - Diffusion control for rough boundary
 - Mixed control (diffusion or interface reaction) for faceted boundary

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Experimental Supports for the Principle

Experimental Observations and Interpretations (Single Phase Systems)

• Effect of Δg_c (T, Dopant, P_{O₂})

- BaTiO₃ (Lee *et al.*, 2000 (P_{O₂}); Jung *et al.*, 2006 (P_{O₂}); Chang and Kang, 2009 (T), An and Kang, 2011 (Dopant, P_{O₂}); Moon, 2018 (t, P_{O₂}))
- SrTiO₃ (Chung *et al.*, 2002 (Dopant, P_{O₂}))
- Nickel (**Jung *et al.*, 2013, 2014 (T, P_{O₂})**)
- Na_{1/2}Ba_{1/2}TiO₃-BaTiO₃-K_{1/2}Na_{1/2}NbO₃ (Park *et al.*, 2016 (Dopant))
- Na_{1/2}Ba_{1/2}TiO₃-BaTiO₃ (Ko *et al.*, 2016 (T))
- Nickel (Lee *et al.*, 2000 (T))
- Cu (Koo and Yoon, 2001)
- 316L stainless steel (Lee *et al.*, 2001)
- Alumina (Park *et al.*, 2003, 2004 (Dopant))

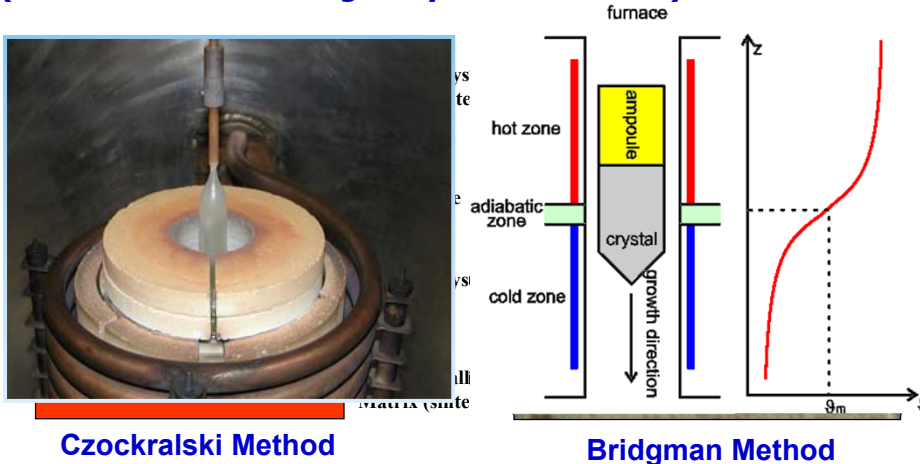
• Effect of Δg_{max}

- BaTiO₃ (**Jung *et al.*, 2003**; Yang *et al.*, 2006)

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Application Example of the Principle

Solid-state Conversion of single crystals (Conventional Methods of Single Crystal Fabrication)



Czochralski Method

Bridgman Method

Kang et al., *J. Am. Ceram. Soc.*, **98** 347 (2015). (Feature article)

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Application Example of the Principle



Kang et al., *J. Am. Ceram. Soc.*, **98** 347 (2015).

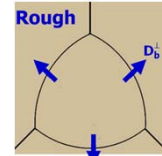
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Concluding Remarks

Microstructural Evolution in Polycrystals Boundary Structure Dependent ($T, P_{O_2}, \text{Dopant}$)

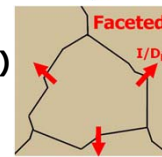
• Rough Boundary:

Linear behavior of boundary migration ($\Delta g_c = 0$)
Stationary GG: **NGG**



• Faceted Boundary:

Nonlinear behavior of boundary migration ($\Delta g_c \neq 0$)
Nonstationary GG: time dependent, typically **AGG**



-Relative contribution of nonlinear region to overall behavior:

$$\Delta g_{\max} \text{ vs } \Delta g_c$$

Kang et al., J. Am. Ceram. Soc., 92, 1464 (2009)
Kang et al., Chapter in Microstructural Design of Advanced Engineering Materials, D. Molodov (ed) Wiley VCH, 299 (2013)

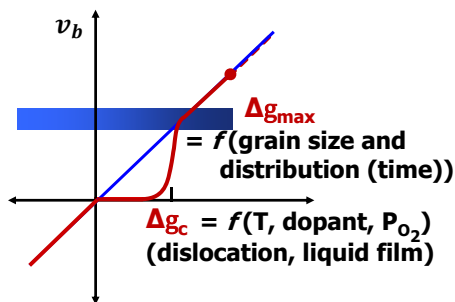
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Concluding Remarks

Interpretation and Prediction of Microstructural Evolution (GG Behavior)

The Mixed Mechanism Principle of Microstructural Evolution

Coupling of Δg_c & Δg_{\max}



- Various types of GG behavior is predicted and observed among NGG, PNGG, SGG, and AGG.
- GG behavior varies with changes in Δg_c (and Δg_{\max}) during sintering (annealing) of systems with faceted boundaries.
eg) Ni and BaTiO₃

Kang et al., J. Am. Ceram. Soc. 98, 347 (2015).
Kang et al., J. Am. Ceram. Soc., 92, 1464 (2009).

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Summary of GG Studies

Liquid Phase Sintering (Ostwald ripening)

- LSW and modified LSW theories from the 60's to 90's for normal grain growth
- Essentially no fundamental studies on AGG until late 90's
- Development of the Mixed Mechanism Theory of grain growth and Mixed Mechanism Principle of microstructural evolution between late 90's and 2000's

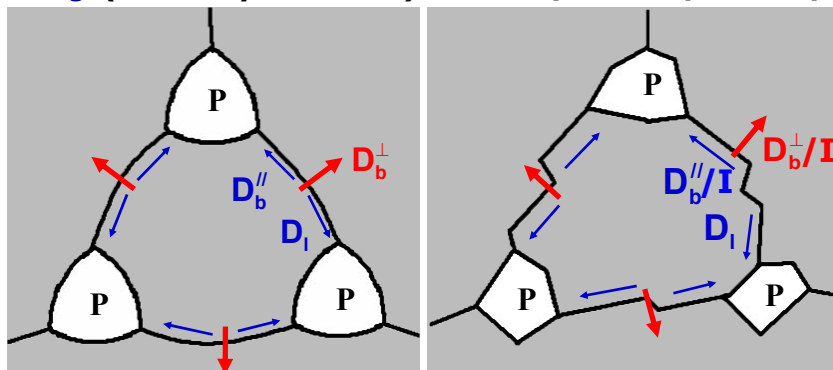
Solid State Sintering

- Theoretical/experimental and simulation studies on GG for pure and impure systems as well as systems with 2nd phase particles and liquid films from the 50's to 2000's
- The early mechanisms fail to explain AGG observed in many different systems.
- The Mixed Control Mechanism of boundary migration and the Mixed Mechanism Principle of microstructural evolution

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Effect of Interface Structure on Densification

Rough(atomically disordered) **Faceted(atomically ordered)**

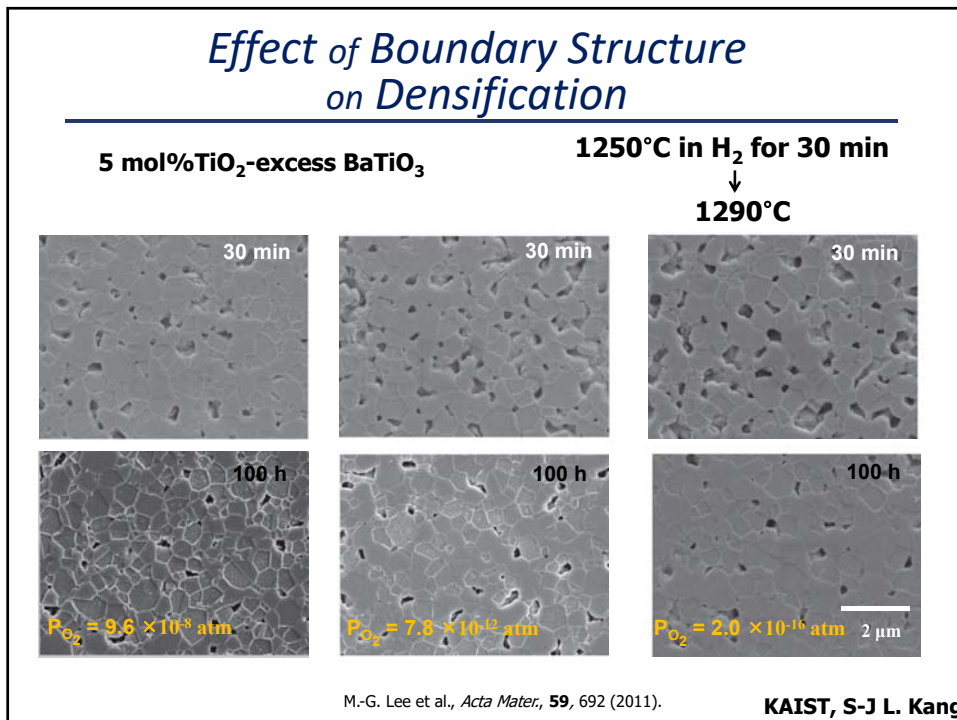
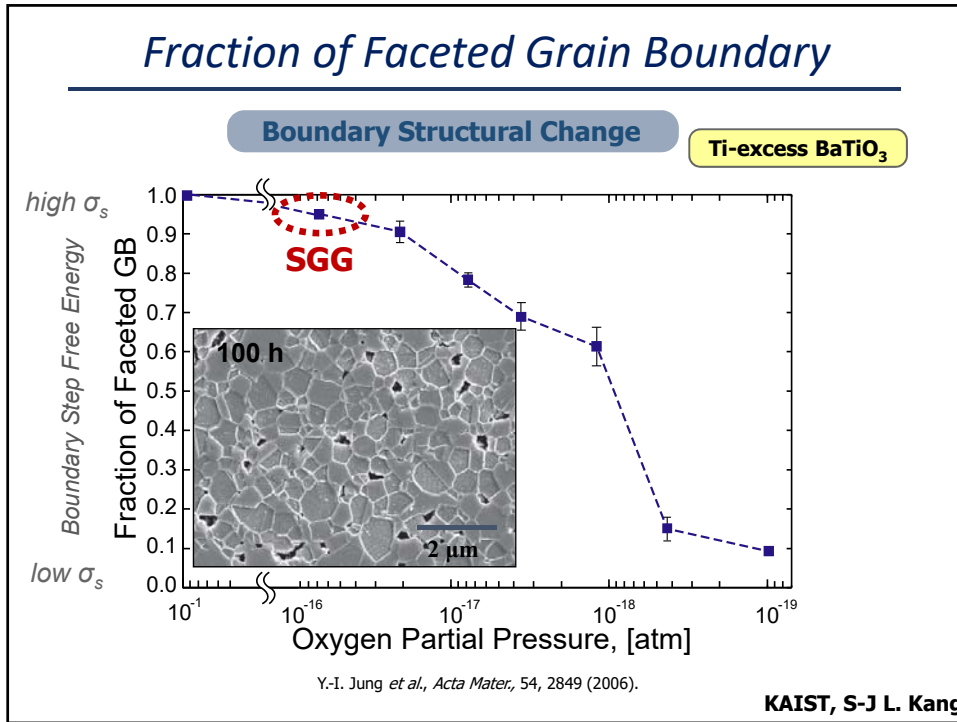


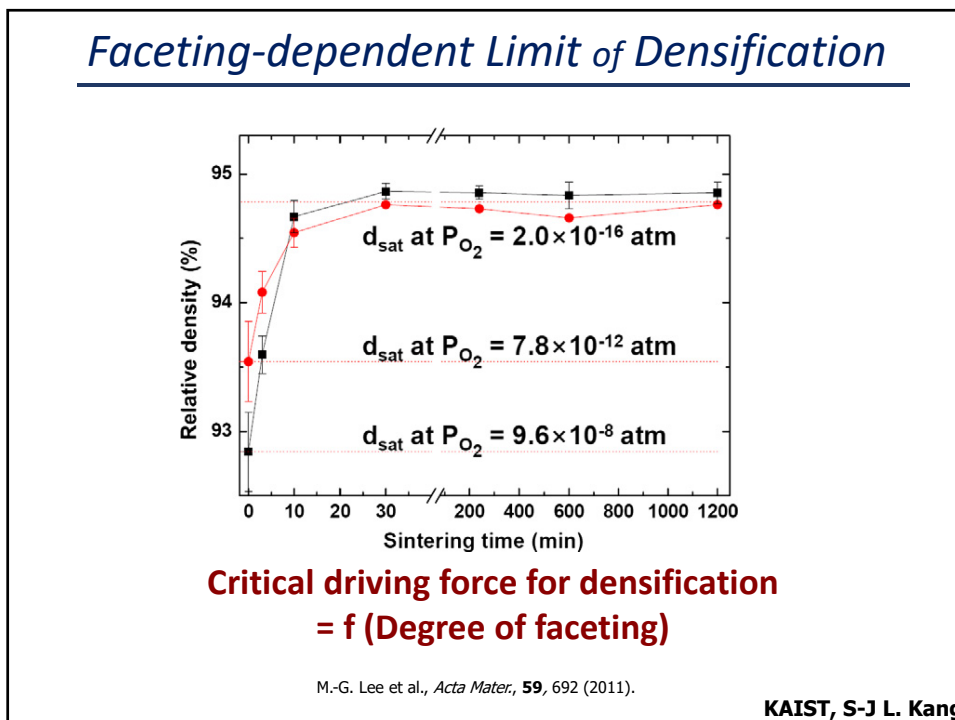
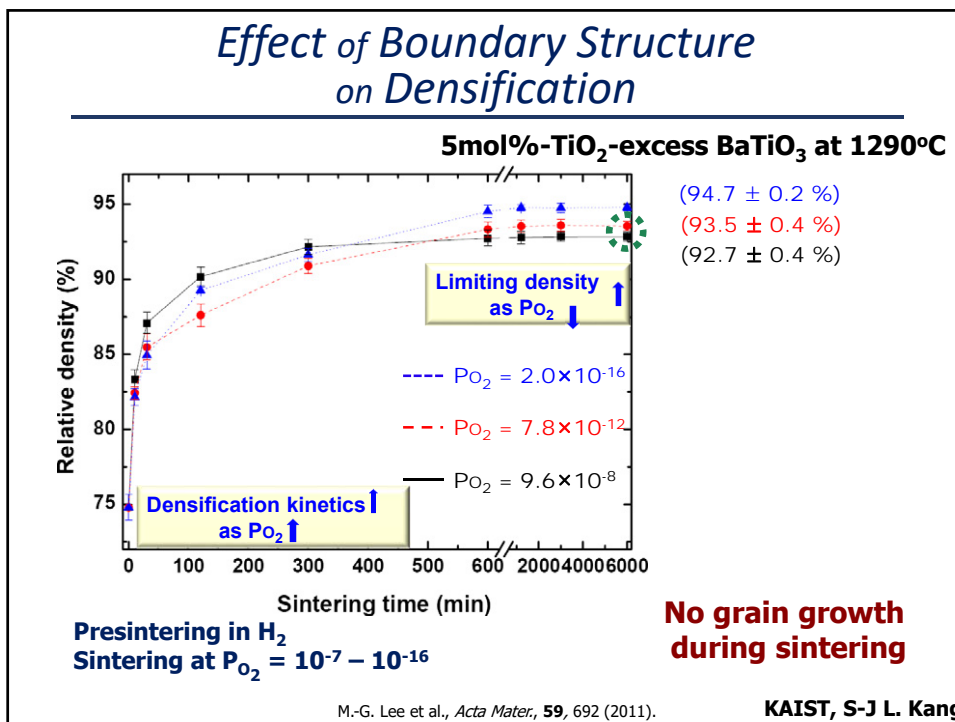
Variables : T, dopant, atmosphere(P_{O_2})

Rate(Δg) : Linear
Diffusion Control

Rate(Δg) : Non-linear
Mixed Control
(Diffusion and Interface Reaction)

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Exercises:

- Dissolution and growth shape of faceted grains
- System NbC-Co:
 - Grain shape at low temperature
 - Growth mechanism of faceted grains
 - Effect of f_i on grain growth behavior
- v_b vs. T for a polycrystal with high solute segregation
- AGG
 - Effects of particle size and temperature

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